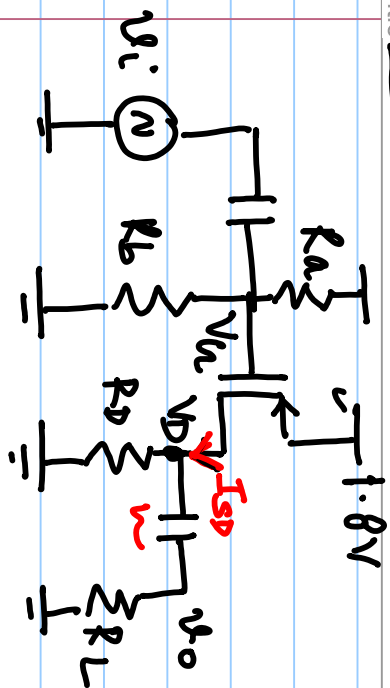


# Tutorial #3



$V_D = 125 \mu A \times 12 K$

$= 1.5 V$

~~$1.5 < 0.6 + 0.7$~~

$-\left(\frac{W}{L}\right) = 20, \quad V_{thp} = -0.7, \quad \mu_p C_{ox} = 50 \mu A/V^2$

$- R_D = 8K \checkmark, \quad R_L = 8K, \quad \frac{R_D}{R_D + R_A} \times 1.8V = 0.6V$

$R_D = 12K, \quad = V_G$

$I_{SD} = \frac{\mu_p C_{ox}}{2} \left(\frac{W}{L}\right) (V_{GS} - |V_{thp}|)^2 \checkmark$

$= \frac{50 \times 10^{-6}}{2} \times \frac{1}{2} \times (1.8 - 0.6 - 0.7)^2$

$= 5 \times 10^{-4} \times 0.5^2$

$= \frac{5}{4} \times 10^{-4} = 125 \mu A$

$V_D = 125 \mu A \times 8K = 0.125 mA \times 8 K = 1V$

$- \quad V_{GS} > |V_{thp}|, \quad V_{SD} > V_{GS} - |V_{thp}| \checkmark$

~~Transistor is in cut-off.~~  $\Rightarrow V_G - V_D > V_G - V_G - |V_{thp}|$

$\Rightarrow V_D < V_G + |V_{thp}| \checkmark$

$1V, \quad 0.6 + 0.7 = 1.3$

$$I_{SD} = \mu_p C_{ox} \left( \frac{W}{L} \right) \left( (V_{GS} - |V_{TP}|) V_{SD} - \frac{V_{SD}^2}{2} \right) = \frac{V_D}{R_p}$$

$$50 \mu A/V^2 \cdot 20 \left( (1.2 - 0.7) (1.8 - V_D) - \frac{(1.8 - V_D)^2}{2} \right) = \frac{V_D}{12k}$$

$$(1000 \mu A/V^2)$$

$$12 \left( 0.5 (1.8 - V_D) - \frac{(1.8 - V_D)^2}{2} \right) = V_D \quad 1.8^2$$

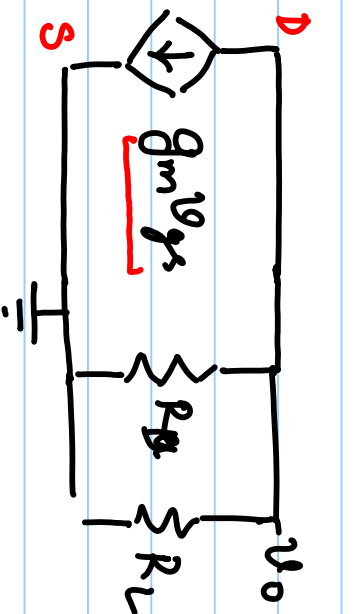
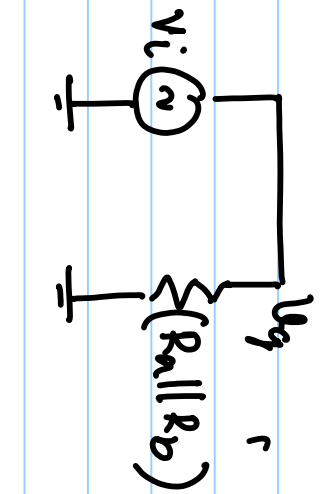
$$12 \left( 0.9 - 0.5 V_D - \frac{(3 \cdot 1.8 + V_D^2 - 3 \cdot 6 V_D)}{2} \right) = V_D$$

$$12 (1.3 V_D - 0.5 V_D^2 - 0.72) = V_D$$

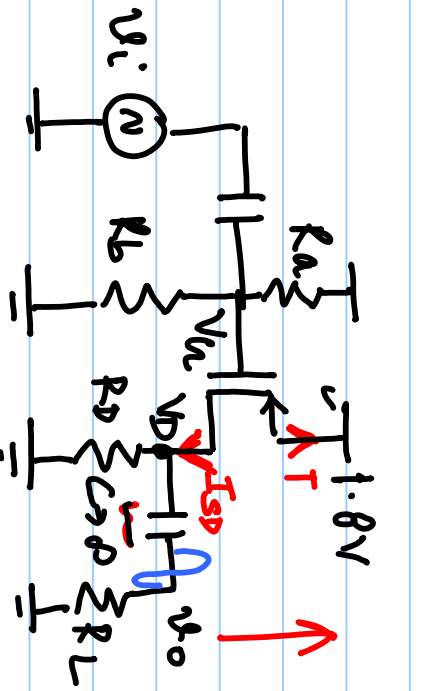
$$I_{SD} = 125 \mu A, \quad \frac{W}{L} = 20, \quad \mu_{p} C_{ox} = 50 \mu A/V^2, \quad V_{thp} = -0.7 V$$

$$g_m = \frac{2 I_{SD}}{V_{GS} - (V_{thp})} = \frac{2 \times 0.125 \text{ mA}}{1.8 - 0.6 - 0.7} = \frac{0.25 \text{ mA}}{0.5 \text{ V}} = 0.5 \text{ mA/V}$$

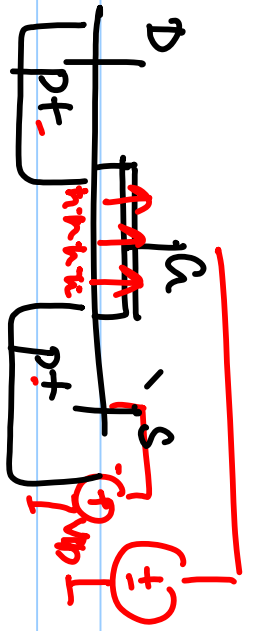
$$r_{ds} = \frac{1}{\partial I_{DS} / \partial V_{DS}} = \infty$$



$$\frac{v_o}{v_i} = -g_m (R_D || R_L) = -0.5 \text{ mA/V} \times 4 \text{ k}\Omega = -2 \text{ V/V}$$



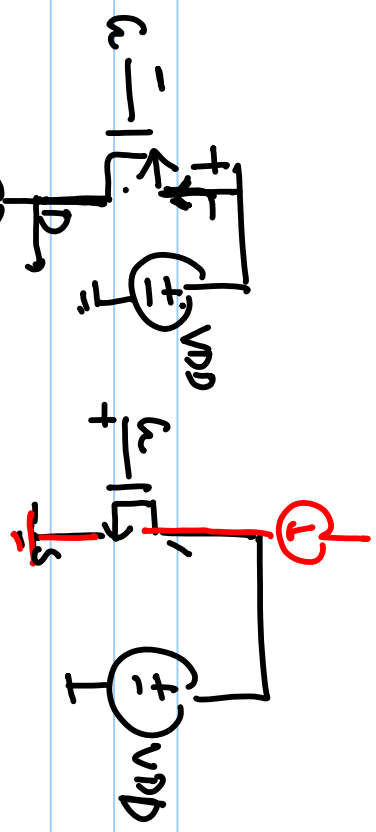
$$\begin{aligned} - & V_{GS} - |V_{thp}| > 0 \quad \checkmark \\ - & V_{SD} > V_{GS} - |V_{thp}| \quad \checkmark \\ & V_D \leq V_G + |V_{thp}| \quad \checkmark \end{aligned}$$



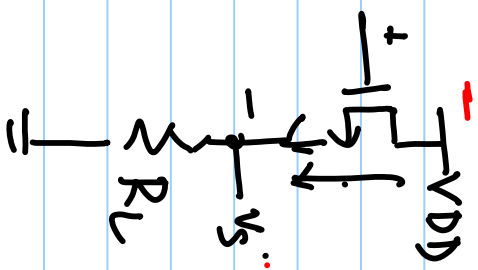
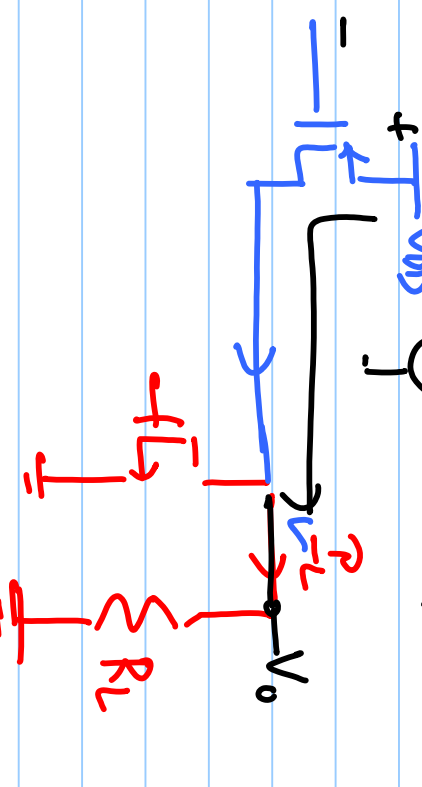
n-type



$$V_{as} < V_{thp}$$



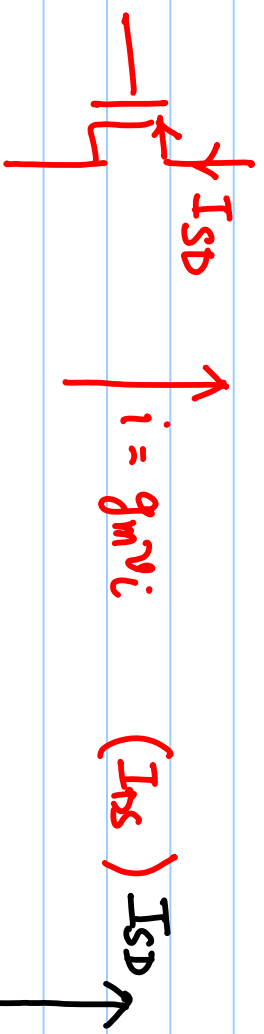
NMOS



$$\begin{aligned}
 & - V_{SC} - |V_{thp}| > 0 \\
 & - V_{SD} \geq V_{SC} - |V_{thp}| \\
 & - V_D \leq V_a + |V_{thp}| \\
 & - \tilde{I}_{SD} - g_m v_i \geq 0
 \end{aligned}
 \left| \begin{aligned}
 & - 1.8 - (0.6 + v_i) - 0.7 > 0 \\
 & v_i < 0.5 \\
 & - 0.125 \text{ mA} - 0.5 \frac{\text{mA}}{\text{V}} v_i \geq 0
 \end{aligned} \right.$$

$$v_i \leq \frac{0.125}{0.5}$$

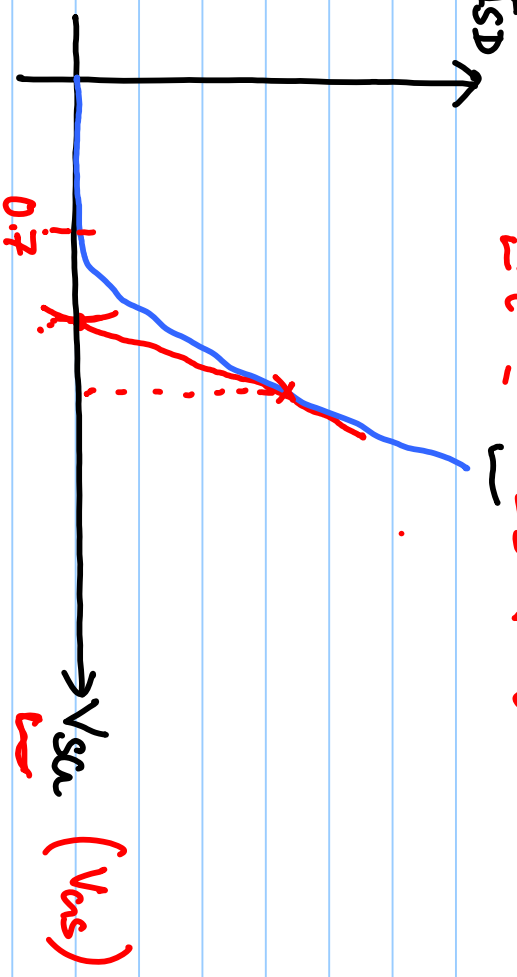
$$v_i \leq 0.25 \text{ V}$$

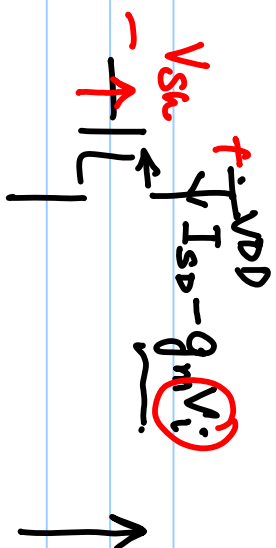
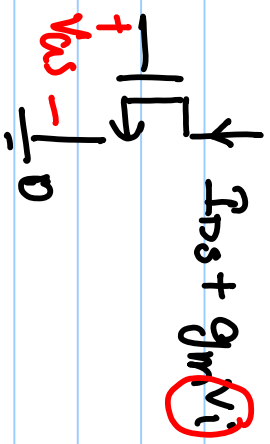


$$1.0 \text{ V} - 2 \text{ V/V} \times v_i \leq 0.6 + v_i + 0.7$$

$$-0.3 \leq 3 v_i$$

$$-0.1 \text{ V} \leq v_i$$





$$-0.1V \leq v_i \leq 0.25V$$

$$-0.5V \leq v_o \leq 0.2V$$

$$1 - 0.5 \leq 1.0 + v_o \leq 1 + 0.2$$

$$0.5 \leq v_D \leq 1.2$$